NP0G1AE

Silicon PNP epitaxial planar type

For digital circuits

■ Features

- SSS Mini type 6-pin package, reduction of the mounting area and assembly cost by one half
- Maximum package height (0.4 mm) contributes to develop thinner equipments

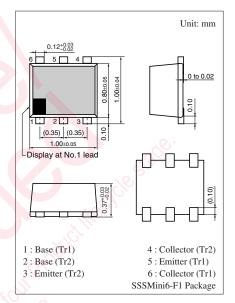
■ Basic Part Number

• UNR31AE × 2 elements

■ Absolute Maximum Ratings $T_a = 25$ °C

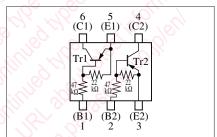
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-50	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Collector current	I_{C}	-80	mA
Total power dissipation *	P _T	125	mW
Junction temperature	T _j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Note) *: Measuring on substrate at 17 mm × 10 mm × 1 mm



Marking Symbol: 6H

Internal Connection

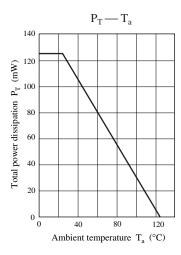


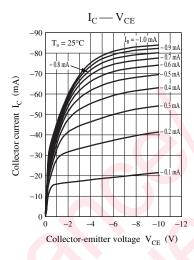
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

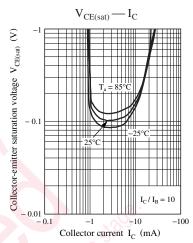
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -6 \text{ V}, I_{C} = 0$			- 0.2	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	60			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V _{OH}	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V _{OL}	$V_{CC} = -5 \text{ V}, V_B = -6.0 \text{ V}, R_L = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R ₁		-30%	47	+30%	kΩ
Resistance ratio	R_1 / R_2		1.7	2.14	2.6	
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

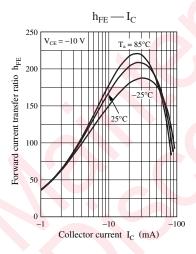
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

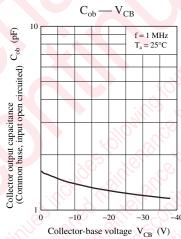
Panasonic

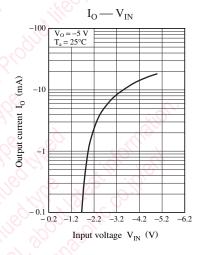


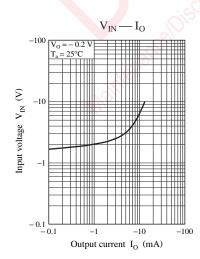












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